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What is claimed is:

1. An electrolytic polishing apparatus for electrolytic polishing a conductive film subject to polishing formed on a substrate, comprising:
5 a resistance measuring unit for measuring electric resistance of said film subject to polishing.
2. The electrolytic polishing apparatus according to claim 1, further comprising a termination point detecting unit for detecting
10 a termination point of polishing by reading a variation of resistance value measured by said resistance measuring unit.
3. The electrolytic polishing apparatus according to claim 2, further comprising a polishing control portion for terminating
15 electrolytic polishing based on a termination point of polishing detected by said termination point detecting unit.
4. An electrolytic polishing method for electrolytic polishing a conductive film subject to electrolytic polishing formed on a
20 substrate, comprising the following step of:

terminating said electrolytic polishing upon detecting a variation of resistance value of said film subject to electrolytic polishing in the process of electrolytic polishing and determining a termination point of said electrolytic polishing.

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5. A wafer comprising;

a substrate:

a first conductive layer formed on a surface of said substrate;

a terminal connection area connected with terminals of a
10 resistance measuring unit, said terminal connection area formed on
surface-side periphery of said first conductive layer; and

a second conductive layer subjected to selective electrolytic
polishing against said first conductive layer, said second conductive
layer formed on a surface of said first conductive layer except on
15 said terminal connection area.

6. A polishing apparatus polishing a conductive film formed on
a substrate, comprising a means for measuring electric resistance
of said film.

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7. The polishing apparatus according to claim 1, further comprising a means for detecting a termination point of polishing by detecting a variation of the electric resistance measured by said means for measuring electric resistance.

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8. The polishing apparatus according to claim 2, further comprising a means for terminating electrolytic polishing based on a termination point detected by said means for detecting the termination point of polishing.

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9. A method for polishing a conductive film formed on a substrate, comprising the following step of:

terminating polishing upon determining a termination point of polishing based on a variation of electric resistance of said film.

15 during said polishing.

10. A wafer comprising:

a substrate;

a first conductive layer formed on a surface of said substrate;

20 a means for connecting said first conductive layer with a

means for measuring electric resistance; and

a second conductive layer formed on a surface of said first conductive layer, wherein said second conductive layer is subject to polishing against said first conductive layer.

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